JCT612C 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT612C of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. Especially recommended for use on solid state relay, motorcycle, power charger, Tools etc. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} / V_{RRM}	600	V
I_{GT}	≤15	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit

Average gate power dissipation (T_j = 125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j = 25; non-repetitive, off-state; F	V_p	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j = 25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D = 12V R_L = 33Ω	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	V_D = V_{DRM} T_j = 25 R_L = 3.3 kΩ	0.2	-	-	V
I_L	I_G = 1.2 I_{GT}	-	-	60	mA

ORDERING INFORMATION

J C6T 12C

JieJie Microelectronics Co., Ltd

SCRs

6: VDRM MA(ER).61R4.044 0K14.04 70SN AT

ORDERING INFORMATION

PACKAGE MECHANICAL DATA